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Preface

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Physics Procedia 11 (2011) 1-6

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### **Contents**

| Y. Maeda ·····  |
|---|
| Organizers page ······ 8  |
| Al- and Cu-doped BaSi <sub>2</sub> films on Si(111) substrate by molecular beam epitaxy and evaluation o                          |
| depth profiles of Al and Cu atoms   |
| M. Ajmal Khan, M. Takeishi, Y. Matsumoto, T. Saito and T. Suemasu ·····11   |
| Magnetoresistance characteristics of Fe <sub>3</sub> Si/CaF <sub>2</sub> /Fe <sub>3</sub> Si heterostructures grown on Si(111) by |
| molecular beam epitaxy grown on Si(111) by molecular beam epitaxy   |
| K. Harada, K. S. Makabe, H. Akinaga and T. Suemasu15  |
| Reduction of carrier concentrations of $\beta$ -FeSi $_2$ films by atomic hydrogen-assisted molecular bean epitaxy                |
| K. Akutsu, M. Suzuno, H. Kawakami and T. Suemasu ······19   |
| Molecular beam epitaxy of $\beta$ -FeSi $_2$ films on Si(111) substrates and its influence on minority-carrie                     |
| diffusion length of Si measured by EBIC   |
| H. Kawakami, M. Suzuno, K. Akutsu, J. Chen, Y. Fuxing, T. Sekiguchi and T. Sueması  |
| Growth of Al-doped p-type BaSi <sub>2</sub> films by molecular beam epitaxy and the effect o                                      |
| high-temperature annealing on their electrical properties   |
| M. Takeishi, Y. Matsumoto, R. Sasaki, T. Saito and T. Suemasu27   |
| Formation of poly-Si layers on AZO/SiO <sub>2</sub> substrates and anti-reflection coating with AZO films fo                      |
| BaSi <sub>2</sub> solar cells   |
| A. Okada, R. Sasaki, Y. Matsumoto, M. Takeisi, T. Saito, K. Toh, N. Usami and   |
| T. Suemasu31  |

| $Influence \ of \ CrSi_2 \ nanocrystals \ on \ the \ electrical \ properties \ of \ Au/Si-p/CrSi_2 \ NCs/Si(111)-n$ |
|---|
| mesa-diodes   |
| N. G. Galkin, L. Dózsa, E. A. Chusovitin, S. A. Dotsenko, B. Pécz and   |
| L. Dobos35  |
|   |
| Ultra high vacuum growth of $CrSi_2$ and $\beta$ -FeSi $_2$ nanoislands and $Si$ top layers on the plasma           |
| modified monocrystalline silicon surfaces   |
| N. G. Galkin, V. M. Astashynski, E. A. Chusovitin, K. N. Galkin, T. A. Dergacheva,                                  |
| A. M. Kuzmitski and E. A. Kostyukevich39  |
| Formation of nanocrystalline CrSi <sub>2</sub> layers in Si by ion implantation and pulsed annealing                |
| R.I. Batalov, R.M. Bayazitov, V.F. Valeev, N.G. Galkin, D.L. Goroshko, K.N. Galkin,                                 |
| E.A. Chusovitin, P.I. Gaiduk, G.D. Ivlev and E.I. Gatskevich ······ 43  |
| The model of the magnesium silicide phase $(2/3 \sqrt{3} \times 2/3 \sqrt{3})$ -R30° on Si(111)                     |
| K. N. Galkin, M. Kumar, S.M. Shivaprasad and N. G. Galkin   |
| K. N. Gaikiii, W. Kumai, S.W. Sinvapiasad and W. G. Gaikii  |
| AES and EELS study of desorption of magnesium silicide films on Si(111)   |
| K. N. Galkin, M. Kumar, S.M. Shivaprasad and N. G. Galkin51   |
| Silicon overgrowth atop low-dimensional $Mg_2Si$ on $Si(111)$ : structure, optical and thermoelectrical properties  |
| K. N. Galkin and N. G. Galkin ·····55   |
| Chemical trends of the band gaps in semiconducting silicon clathrates   |
| Y. Imai and A. Watanabe ·····59   |
| Valence electronic structure of β-FeSi <sub>2</sub> single crystal investigated by photoelectron spectroscopy       |
| using synchrotron radiation   |
| K. Ogawa, M. Sasaki, A. Ohnishi, M. Kitaura, H. Fujimoto, J. Azuma, K. Takahashi and                                |
| M. Kamada ······63  |
| Surface analysis of single-crystalline β-FeSi <sub>2</sub>  |
| Y. Yamada, W. Mao, H. Asaoka, H. Yamamoto, F. Esaka, H. Udono and   |
| T. Tsuru  |

| Antireflection coatings with FeSi <sub>2</sub> layer:Application to spectrally selective infrared emitter     |
|---|
| Y. Kaneko, M. Suzuki, K. Nakajima, K. Kimura, K. Akiyama, K. Harutsugu,                                       |
| H. Wakabayashi and T. Makino71  |
|   |
| Fabrication and characterization of novel Fe(Os)Si <sub>2</sub> semiconductor                                 |
| Y. Gao, H. W. Liu, Y. Lin and G. Shao ······75  |
| Iron silicide photonic crystals and light propagation property  |
| Y. Maeda79  |
| Determination of silicon vacancy in ion-beam synthesized β-FeSi <sub>2</sub>                                  |
| Y. Maeda, T. Ichikawa, T. Jonishi and M. Narumi83   |
| 1. Maeda, 1. Ichikawa, 1. Johishi and M. Naruhi   |
| Transformation from $\epsilon\text{-FeSi}$ to $\beta\text{-FeSi}_2$ in RF-Sputtered FeSi_x Films              |
| N. Kawabata and K. Nakamura87   |
| Influence of Si(111) $\sqrt{3}$ x $\sqrt{3}$ -R30°-Sb surface phase on the formation and conductance of       |
| low-dimensional magnesium silicide layer on Si(111) substrate   |
| D. L. Goroshko, K. N. Galkin and N. G. Galkin91   |
| D. L. Golosiko, K. N. Gaikiii aliu N. G. Gaikiii  |
| Growth, optical and electrical properties of $Ca_2Si$ film grown on $Si(111)$ and $Mg_2Si/Si(111)$ substrates |
| S.A. Dotsenko, D.V. Fomin, K.N. Galkin, D.L. Goroshko and N.G. Galkin95                                       |
| Study on the electronic structure and optical properties of the environmentally friendly                      |
| semiconductor Ca <sub>3</sub> Si <sub>4</sub>   |
| R. Gao and Q. Xie99   |
| Thermoelectric properties of sputtered iron-silicide  |
| S.Nakamura, Y. Marumoto, M. Mimura, D. Sugiyama, T. Kittaka, K. Kametomo, N. Yasui                            |
| and K. Takarabe   |
| Electrical properties of Ca <sub>2</sub> Si sintered compact synthesized by spark plasma sintering            |
| C. Wen, T. Nonomura, A. Kato, Y. Kenichi, H. Udono, K. Isobe, M. Otake, Y. Kubota,                            |
| T. Nakamura, Y. Hayakawa and H. Tatsuoka ······106  |

| Thermoelectric properties of group VI metal silicide semiconductors   |
|---|
| T. Nonomura, C. Wen, A. Kato, K. Isobe, Y. Kubota, T. Nakamura, M. Yamashita,   |
| Y. Hayakawa and H. Tatsuoka ·····110  |
| $Sr_2SiO_4$ flower-like nanostructures grown by thermal oxidation of $SrSi_2$ with Ga droplets                          |
| Q. Yang, M. Tanaka, S. Liang, K. Ogino, T. Yasuda and H. Tatsuoka ······114   |
| Effects of annealing temperature on the structure and surface feature of BaSi <sub>2</sub> films grown or               |
| Si(111) substrates  |
| Z. Yang, Z. Hao and Q. Xie ·····118   |
| Thermal Process of Iron Silicides prepared by Magnetron sputtering  |
| J. Zhang, Q. Xie, Y. Liang, W. Zeng, Q. Xiao, Q. Chen, D. Ma, Y. Wang, K. Yamada and                                    |
| J. Luo122   |
| Atomic Diffusion in the interface of Fe/Si prepared by Magnetron sputtering   |
| J. Zhang, Q. Xie, Y. Liang, W. Zeng, Q. Xiao, Q. Chen, V. Borjanović, M. Jakšić,  |
| M. Karlusic, B. Gržeta, K. Yamada and J. Luo ······126  |
| Influence of sputtering power on the structural and morphological properties of semiconducting Mg <sub>2</sub> Si films |
| Q. Xiao, Q. Xie, Z. Yu and K. Zhao ·····130   |
| First-principles calculations on the electronic structure and optical properties of $Mg_2Si$ epitaxial on $Si$ (111)    |
| Q. Chen and Q. Xie134   |
| Preparation and electrical properties of Mn silicides by reaction of MnCl <sub>2</sub> and Si powder                    |
| J. Hu, C. Zhang, W. Li, S. Guan and H. Tatsuoka ······138   |
| On the role of induced impurity potential of $\beta$ -FeSi <sub>2</sub>   |
| S. Kondo M. Hasaka and T. Morimura ······142  |
| Ab-initio calculation of (101) and (100) surface for β-FeSi <sub>2</sub>  |
| S. Tanimoto and T. Nagano ·····146  |

| Surface characterization of homoepitaxial $\beta$ -FeSi $_2$ film on $\beta$ -FeSi $_2$ (111) substrate by X-ray                   |
|--|
| photoelectron and absorption spectroscopy  |
| F. Esaka, H. Yamamoto, H. Udono, N. Matsubayashi, K. Yamaguchi, S. Shamoto,  |
| M. Magara and T. Kimura ······150  |
| Current-induced magnetization switching in Fe <sub>3</sub> Si/FeSi <sub>2</sub> superlattices                                      |
| S. Hirakawa, K. Sakai, T. Sonoda, K. Takeda and T. Yoshitake ······154   |
| The effect of crystalline structure on photoluminescence of the $\beta$ -FeSi $_2$ film prepared by pulsed laser                   |
| deposition using two types of target   |
| M. Zakir Hossain, H. Katsumata and S. Uekusa ·····158  |
| Behavior of nickel silicide in multi-crystalline silicon for solar cells   |
| T. Tachibana, T. Sameshima, K. Arafune, Y. Ohshita and A. Ogura ······163  |
| Phonon properties of $\beta$ -FeSi <sub>2</sub> and photoluminescence  |
| Y. Maeda, T. Nakajima, B. Matsukura, T. Ikeda and Y. Hiraiwa ······167   |
| Preparation of Schottky contacts on n-type Mg <sub>2</sub> Si single crystalline substrate   |
| K.Sekino, M.Midonoya, H.Udono and Y.Yamada ······171   |
| Surface structures of $\beta$ -FeSi $_2$ formed by heat-treatment in ultra-high vacuum and their influence on homoepitaxial growth |
| S. Matsumura, K. Ochiai, H. Udono, F. Esaka, K. Yamaguchi, H. Yamamoto and K. Houjo ······174                                      |
| Effect of temperature modulation during temperature gradient solution growth of β-FeSi <sub>2</sub>                                |
| Y. Ujiie, K. Nakamori, S. Mashiko, H. Udono and T. Nagata ······177  |
| Temperature dependence of direct transition energies in $\beta$ -FeSi <sub>2</sub> epitaxial films on Si(111) substrate            |
| K. Noda, Y. Terai, K. Yoneda and Y. Fujiwara ·····181  |
| Photoluminescence and photoreflectance studies in Si/β-FeSi <sub>2</sub> /Si(001) double heterostructure                           |
| K. Yoneda, Y. Terai, K. Noda, N. Miura and Y. Fujiwara ·····185  |

| $Fabrication \ of \ BaSi_2 \ films \ on \ transparent \ CaF_2(111) \ substrates \ by \ molecular \ beam \ epitaxy \ for \ optical$ |
|--|
| characterization   |
| K. Toh, T. Saito, M. Ajmal Khan, A. Okada, N. Usami and T. Suemasu ······189   |
| Toward the epitaxial growth of ferromagnetic $\gamma$ -Fe <sub>4</sub> N on Si(100) substrate by molecular beam epitaxy            |
| G. H. Lee, K. Ito and T. Suemasu ————————————————————————————————————  |
| Metal induced crystallization of amorphous silicon for photovoltaic solar cells  |
| D. Van Gestel, I. Gordon and J. Poortmans ······196  |
| Magnetooptical properties of iron based Heusler alloy epitaxial films on Ge(111)   |
| Y. Maeda, T. Ikeda, T. Ichikawa, T. Nakajima, B. Matsukura, T. Sadoh and   |
| M. Miyao ······200   |